

# 2N5832

## Features

- Through Hole Package

Pin Configuration  
 Bottom View



### Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
<b>OFF CHARACTERISTICS</b>				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=300mA_{dc}$ )	140		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	160		Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0		Vdc
$I_{CBO}$	Collector-Base Breakdown Current ( $V_{CE}=120Vdc$ )		50	nAdc

### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain*  ( $I_C=10mA_{dc}$ , $V_{CE}=5.0Vdc$ )	175	500	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=10mA_{dc}$ )		0.2	Vdc

### SMALL-SIGNAL CHARACTERISTICS

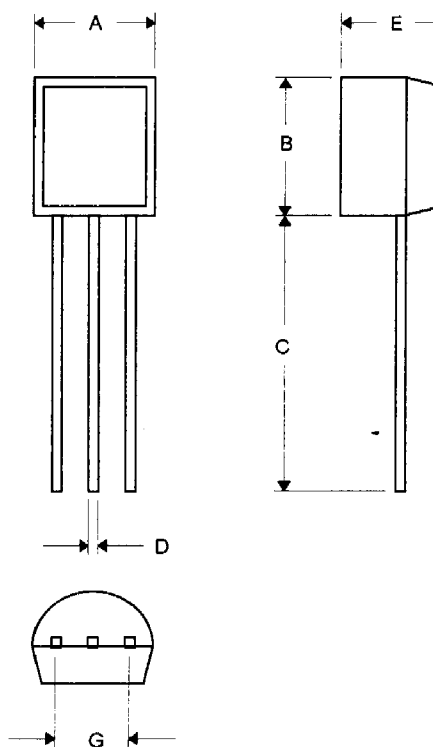
$f_T$	Current Gain-Bandwidth Product ( $I_C=10mA_{dc}$ )	100		MHz
$C_{ob}$	Output Capacitance		4.0	pF
NF	Noise Figure		---	dB

**Note:** Maximum at typical JEDEC condition

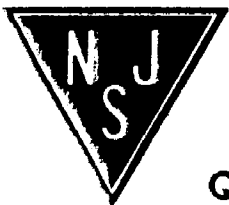
$V_{(BR)CE} @ R=10 \text{ OHMS}$

## Plastic-case Bipolar NPN Transistor

TO-92



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	



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